DATA SHEET

TDA8571J

4 × 40 W BTL quad car radio power amplifier

Product specification
Supersedes data of 1998 Mar 13

2002 Mar 05

Philips
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4 × 40 W BTL quad car radio power amplifier

TDA8571J

FEATURES

- Requires very few external components
- High output power
- Low output offset voltage
- Fixed gain
- Diagnostic facility (distortion, short-circuit and temperature pre-warning)
- Good ripple rejection
- Mode select switch (operating, mute and standby)
- Load dump protection
- Short-circuit safe to ground and to V_P and across the load
- Low power dissipation in any short-circuit condition
- Thermally protected
- Reverse polarity safe
- Electrostatic discharge protection
- No switch-on/switch-off plop
- Flexible leads
- Low thermal resistance
- Pin compatible with the TDA8568Q, except for the gain.

GENERAL DESCRIPTION

The TDA8571J is a integrated class-B output amplifier contained in a 23-lead Single-In-Line (SIL) plastic power package. It contains four amplifiers in a BTL configuration, each with a gain of 34 dB. The output power is 4 × 40 W (EIAJ) into a 4 Ω load.

APPLICATIONS

- Primarily developed for car radio applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_P	operating supply voltage		6	14.4	18	V
I_{ORM}	repetitive peak output current		–	–	7.5	A
$I_{q(tot)}$	total quiescent current		–	200	–	mA
I_{stb}	standby current		–	0.2	100	μA
I_{sw}	switch-on current		–	–	80	μA
$\lvert Z_i \rvert$	input impedance		25	30	–	kΩ
$P_{o(EIAJ)}$	EIAJ output power	THD = maximum	–	40	–	W
SVRR	supply voltage ripple rejection	R_s = 0 Ω	–	50	–	dB
α_{cs}	channel separation	R_s = 10 kΩ	–	50	–	dB
$G_{v(cl)}$	closed-loop voltage gain		33	34	35	dB
$V_{n(o)}$	noise output voltage	R_s = 0 Ω	–	–	170	μV
$\lvert V_{OS} \rvert$	DC output offset voltage	MUTE	–	–	80	mV
$\lvert \Delta V_{OS} \rvert$	delta DC output offset voltage	ON ↔ MUTE	–	–	80	mV

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
TDA8571J	DBS23P	plastic DIL-bent-SIL power package; 23 leads (straight lead length 3.2 mm)	SOT411-1

BLOCK DIAGRAM

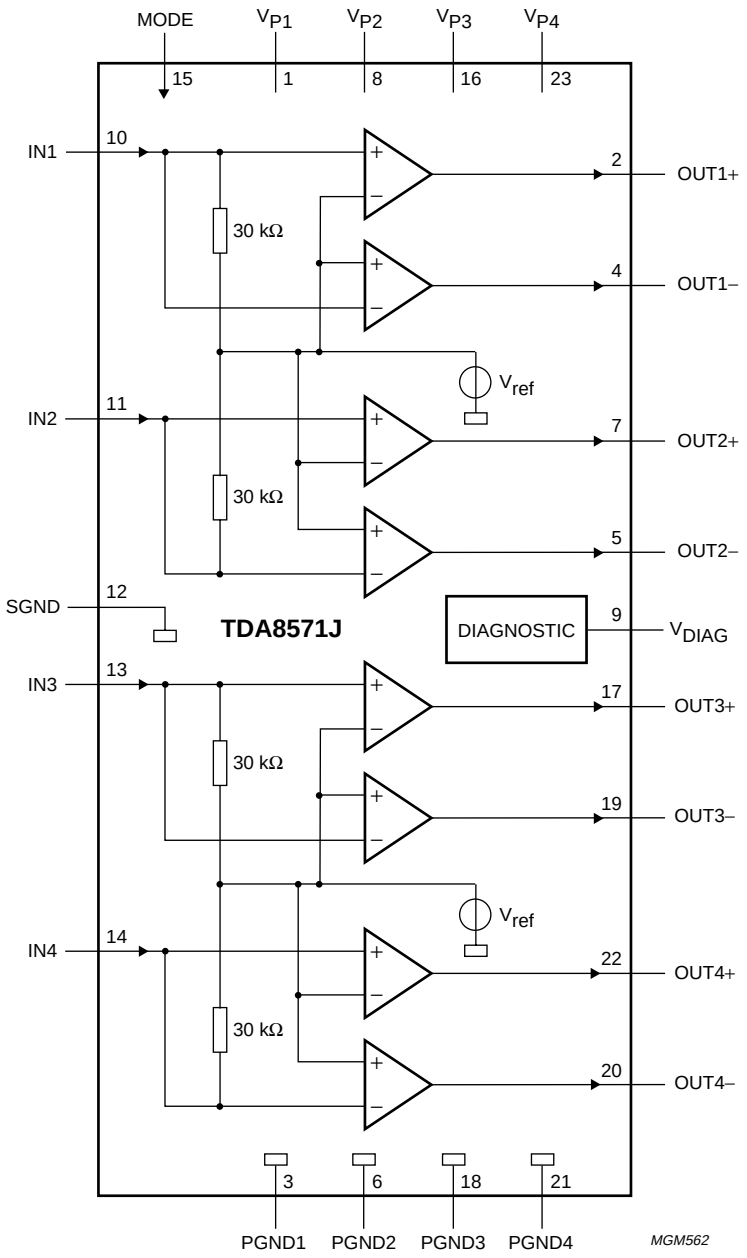


Fig.1 Block diagram.

PINNING

SYMBOL	PIN	DESCRIPTION
V_{P1}	1	supply voltage 1
OUT1+	2	output 1+
PGND1	3	power ground 1
OUT1–	4	output 1–
OUT2–	5	output 2–
PGND2	6	power ground 2
OUT2+	7	output 2+
V_{P2}	8	supply voltage 2
V_{DIAG}	9	diagnostic output
IN1	10	input 1
IN2	11	input 2
SGND	12	signal ground
IN3	13	input 3
IN4	14	input 4
MODE	15	mode select switch input
V_{P3}	16	supply voltage 3
OUT3+	17	output 3+
PGND3	18	power ground 3
OUT3–	19	output 3–
OUT4–	20	output 4–
PGND4	21	power ground 4
OUT4+	22	output 4+
V_{P4}	23	supply voltage 4

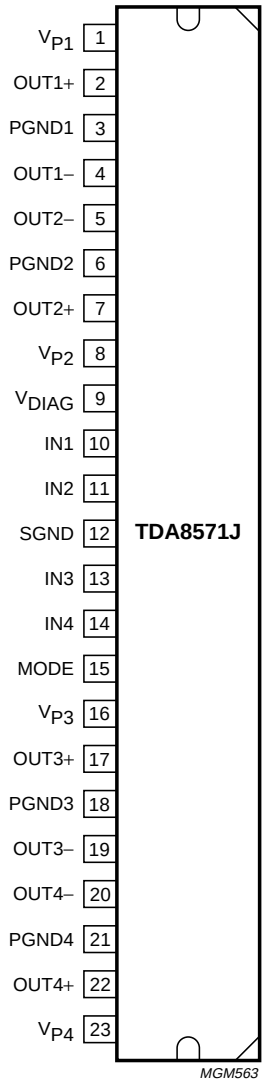


Fig.2 Pin configuration.

FUNCTIONAL DESCRIPTION

The TDA8571J contains four identical amplifiers which can be used for bridge applications. The gain of each amplifier is fixed at 34 dB.

Mode select switch (pin MODE)

- Standby: low supply current (<100 μA)
- Mute: input signal suppressed
- Operating: normal on condition.

Since this pin has a low input current (<80 μA), a low cost supply switch can be applied.

To avoid switch-on plops, it is advised to keep the amplifier in the mute mode during ≥150 ms (charging of the input capacitors at pins IN1, IN2, IN3 and IN4. When switching from standby to mute, the slope should be at least 18 V/s. This can be realized by:

- Microprocessor control
- External timing circuit (see Fig.3).

Diagnostic output (pin V_{DIAG})

DYNAMIC DISTORTION DETECTOR (DDD)

At the onset of clipping of one or more output stages, the dynamic distortion detector becomes active and pin V_{DIAG} goes LOW. This information can be used to drive a sound processor or DC volume control to attenuate the input signal and so limit the distortion. The output level of pin V_{DIAG} is independent of the number of channels that are clipping (see Fig.4).

SHORT-CIRCUIT DIAGNOSTIC

When a short-circuit occurs at one or more outputs to ground or to the supply voltage, the output stages are switched off until the short-circuit is removed and the device is switched on again, with a delay of approximately 10 ms after removal of the short-circuit. During this short-circuit condition, pin V_{DIAG} is continuously LOW.

When a short-circuit occurs across the load of one or more channels, the output stages are switched off during approximately 10 ms. After that time it is checked during approximately 50 μs to determine whether the short-circuit is still present. Due to this duty cycle of 50 μs/10 ms the average current consumption during this short-circuit condition is very low.

During this short-circuit condition, pin V_{DIAG} is LOW for 10 ms and HIGH for 50 μs (see Fig.5). The protection circuits of all channels are coupled. This means that if a short-circuit condition occurs in **one** of the channels, **all** channels are switched off. Consequently, the power dissipation in any short-circuit condition is very low.

TEMPERATURE PRE-WARNING

When the virtual junction temperature T_{vj} reaches 145 °C, pin V_{DIAG} goes LOW.

OPEN-COLLECTOR OUTPUTS

The diagnostic pin has an open-collector output, so more devices can be tied together. An external pull-up resistor is needed.

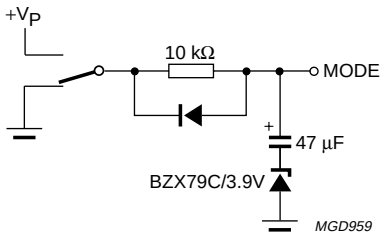


Fig.3 Mode select switch circuitry.

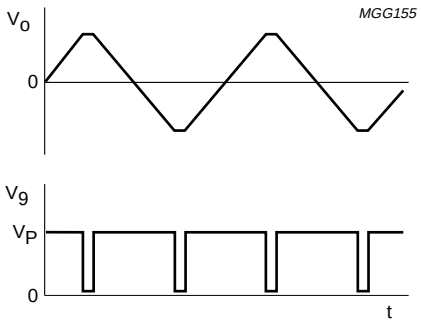


Fig.4 Distortion detector waveform.

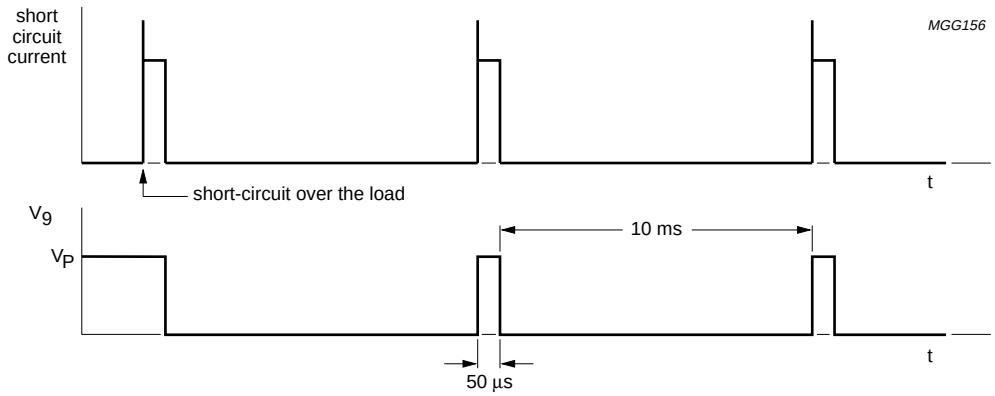


Fig.5 Short-circuit waveform.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_P	supply voltage	operating	–	18	V
		non-operating	–	30	V
		load dump protection; during 50 ms; $t_r \geq 2.5$ ms	–	45	V
$V_{sc(safe)}$	short-circuit safe voltage		–	18	V
V_{rp}	reverse polarity voltage		–	6	V
I_{OSM}	non-repetitive peak output current		–	10	A
I_{ORM}	repetitive peak output current		–	7.5	A
P_{tot}	total power dissipation		–	60	W
T_{stg}	storage temperature		–55	+150	°C
T_{amb}	ambient temperature		–40	+85	°C
T_{vj}	virtual junction temperature		–	150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient in free air	40	K/W
$R_{th\ j\text{-}c}$	thermal resistance from junction to case (see Fig.6)	1	K/W

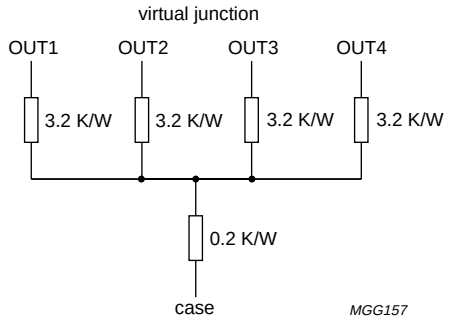


Fig.6 Equivalent thermal resistance network.

QUALITY SPECIFICATION

In accordance with *"General Quality Specification For Integrated Circuits (SNW-FQ-611D)"*.

DC CHARACTERISTICS

V_P = 14.4 V; T_{amb} = 25 °C; measured in Fig.7; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supply						
V_P	supply voltage	note 1	6	14.4	18	V
$I_{q(tot)}$	quiescent current	$R_L = \infty$	–	200	360	mA
Operating condition						
V_{MODE}	mode select switch level		8.5	–	V_p	V
I_{MODE}	mode select switch current	V_{MODE} = 14.4 V	–	30	80	μA
V_O	output voltage	note 2	–	7.0	–	V
Mute condition						
V_{MODE}	mode select switch level		3.3	–	6.4	V
V_O	output voltage	note 2	–	7.0	–	V
$\lvert V_{OS} \rvert$	DC output offset voltage	MUTE	–	–	80	mV
$\lvert \Delta V_{OS} \rvert$	delta DC output offset voltage	ON ↔ MUTE	–	–	80	mV
Standby condition						
V_{MODE}	mode select switch level		0	–	2	V
I_{stb}	standby current		–	0.2	100	μA
Diagnostic						
V_{DIAG}	diagnostic output voltage	during any fault condition	–	–	0.6	V
T_{vj}	temperature pre-warning	V_{DIAG} = 0.6 V	–	145	–	°C

Notes

1. The circuit is DC adjusted at V_P = 6 to 18 V and AC operating at V_P = 8.5 to 18 V.
2. At 18 V < V_P < 30 V the DC output voltage ≤ $\frac{1}{2}V_P$.

AC CHARACTERISTICS

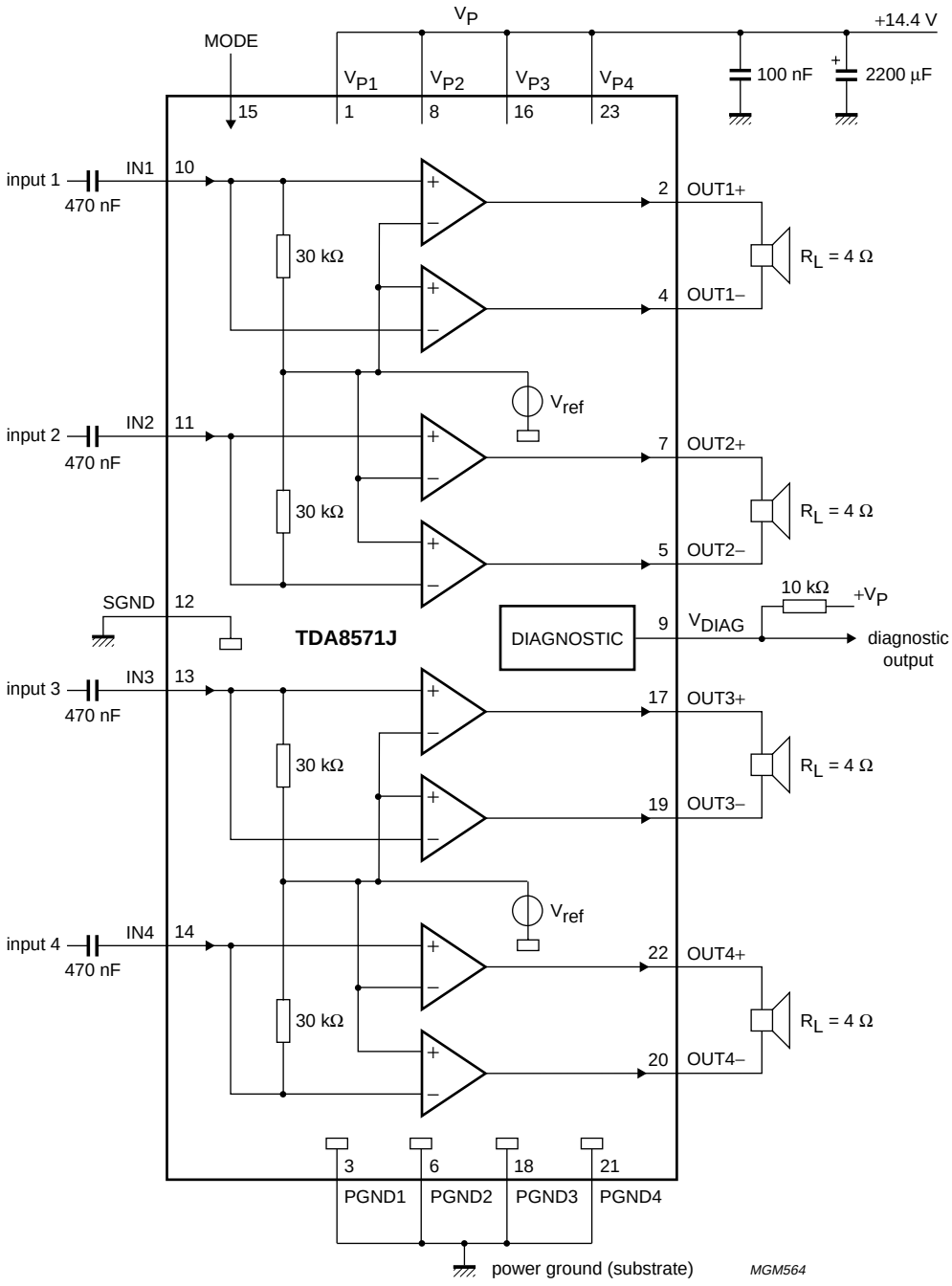
V_P = 14.4 V; R_L = 4 Ω; f = 1 kHz; T_{amb} = 25 °C; measured in Fig.7; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
P_o	output power	THD = 0.5%	16	19	–	W
		THD = 10%	21	26	–	W
		V_P = 13.7 V; THD = 0.5%	–	17.5	–	W
		V_P = 13.7 V; THD = 10%	–	23	–	W
$P_{o(EIAJ)}$	EIAJ output power	THD = maximum; V_i = 2 V (p-p) square wave	35	40	–	W
$P_{o(max)}$	maximum output power	THD = maximum; V_P = 15.2 V; V_i = 2 V (p-p) square wave	40	45	–	W
THD	total harmonic distortion	P_o = 1 W	–	0.1	–	%
		V_{MODE} = 0.6 V; note 1	–	10	–	%
B_p	power bandwidth	THD = 0.5%; P_o = –1 dB with respect to 16 W	–	20 to 20000	–	Hz
$f_{ro(l)}$	low frequency roll-off	at –1 dB; note 2	–	25	–	Hz
$f_{ro(h)}$	high frequency roll-off	at –1 dB	20	–	–	kHz
$G_{v(cl)}$	closed-loop voltage gain		33	34	35	dB
SVRR	supply voltage ripple rejection	R_s = 0 Ω; maximum ripple V_{ripple} = 2 V (p-p)				
		on	40	–	–	dB
		mute	50	–	–	dB
		standby	80	–	–	dB
$\|Z_i\|$	input impedance		25	30	38	kΩ
$V_{n(o)}$	noise output voltage	B = 20 Hz to 20 kHz				
		on; R_s = 0 Ω	–	125	170	μV
		on; R_s = 10 kΩ	–	150	–	μV
		mute; independent of R_s	–	100	–	μV
α_{cs}	channel separation	P_o = 16 W; R_s = 10 kΩ	45	–	–	dB
$\|\Delta G_v\|$	channel unbalance		–	–	1	dB
V_o	output signal in mute	maximum input voltage V_i = 1 V (RMS)	–	–	2	mV

Notes

1. Dynamic Distortion Detector (DDD) active, pin V_{DIAG} is set to LOW level.
2. Frequency response externally fixed.

TEST AND APPLICATION INFORMATION



Special care must be taken in the PCB-layout to separate pin V_{DIAG} from the pins IN1, IN2, IN3 and IN4 to minimize the crosstalk between the clip output and the inputs.

To avoid switch-on plops, it is advised to keep the amplifier in the mute mode during a period of ≥ 150 ms (charging the input capacitors at pins IN1, IN2, IN3 and IN4).

Fig.7 Application circuit diagram.

Test information

Figures 8 to 13 have the following conditions: V_P = 14.4 V; R_L = 4 Ω; f = 1 kHz; 80 kHz filter used; unless otherwise specified.

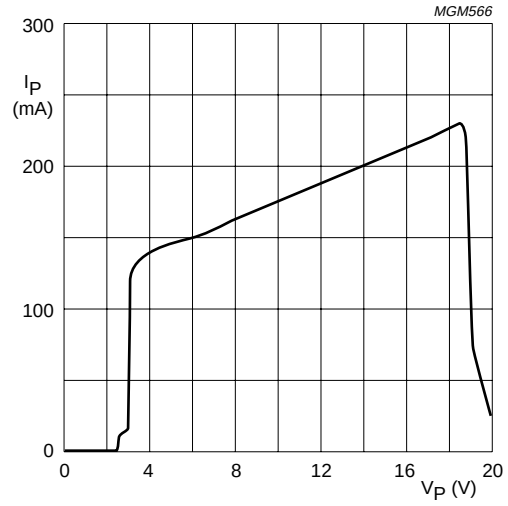
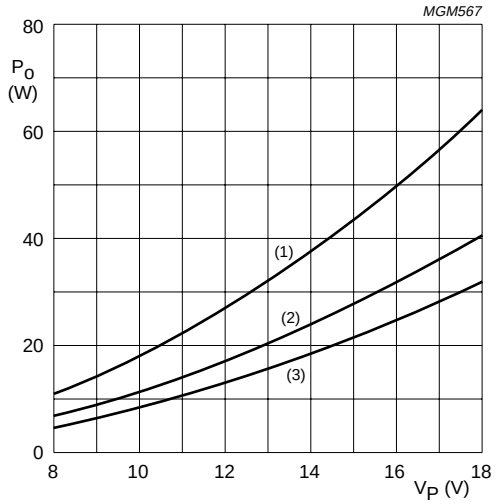
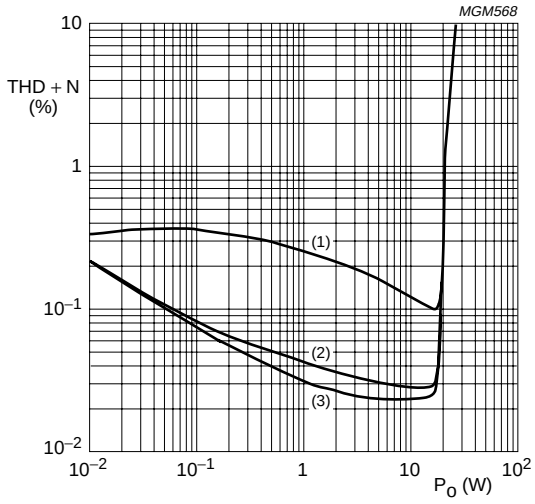


Fig.8 I_P as a function of V_P.



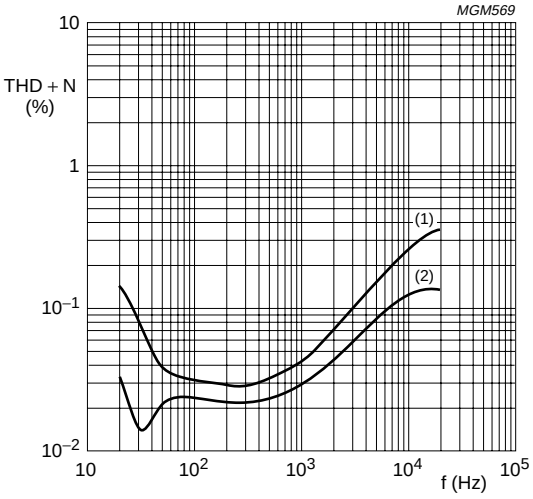
(1) EIAJ; 100 Hz.
(2) THD + N = 10%.
(3) THD + N = 0.5%.

Fig.9 P_o as a function of V_P.



(1) f = 10 kHz.
(2) f = 1 kHz.
(3) f = 100 Hz.

Fig.10 THD + N as a function of P_o.



(1) P_o = 1 W.
(2) P_o = 10 W.

Fig.11 THD + N as a function of frequency.

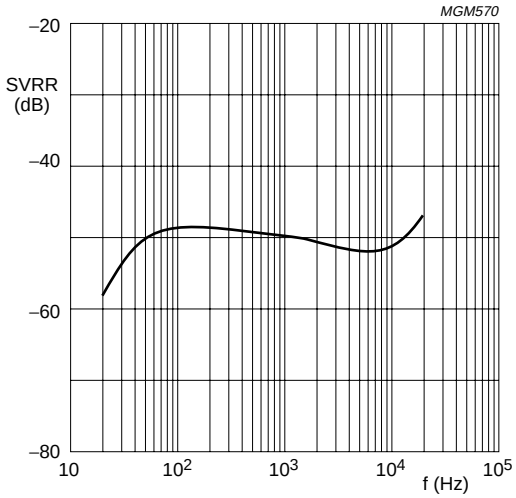
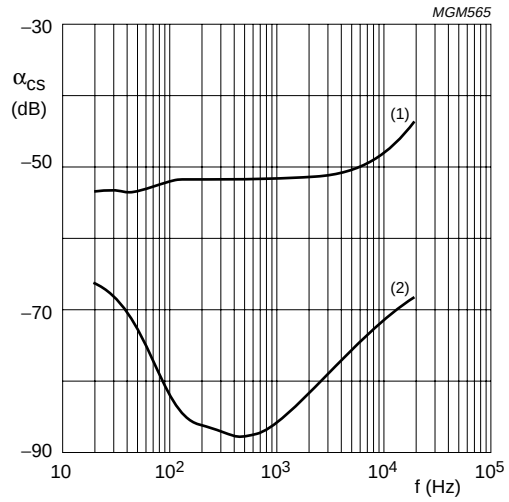


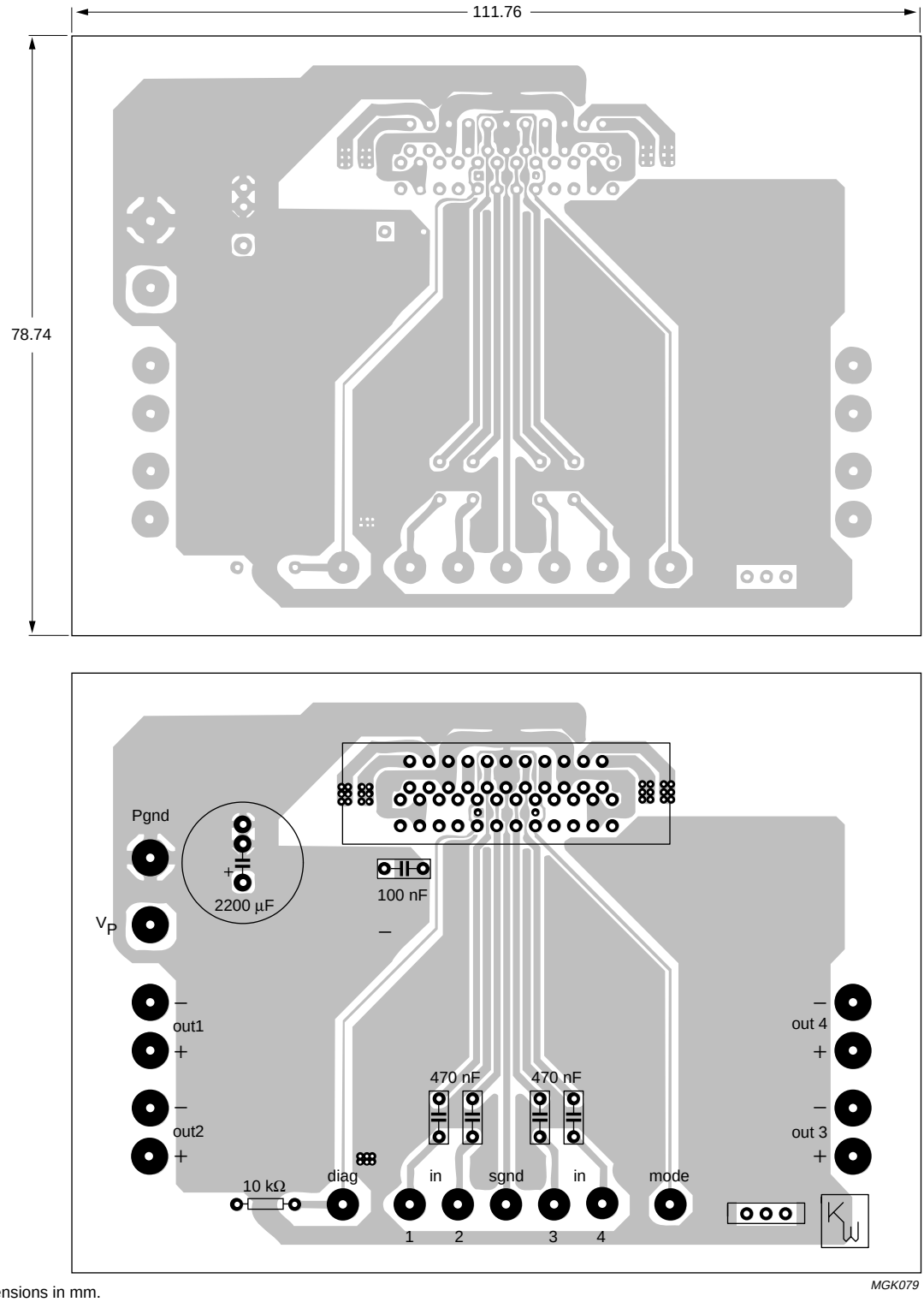
Fig.12 SVRR as a function of frequency.



(1) Between channels 1 and 2 or between channels 3 and 4.
(2) Between channels 1 or 2 and channels 3 or 4.

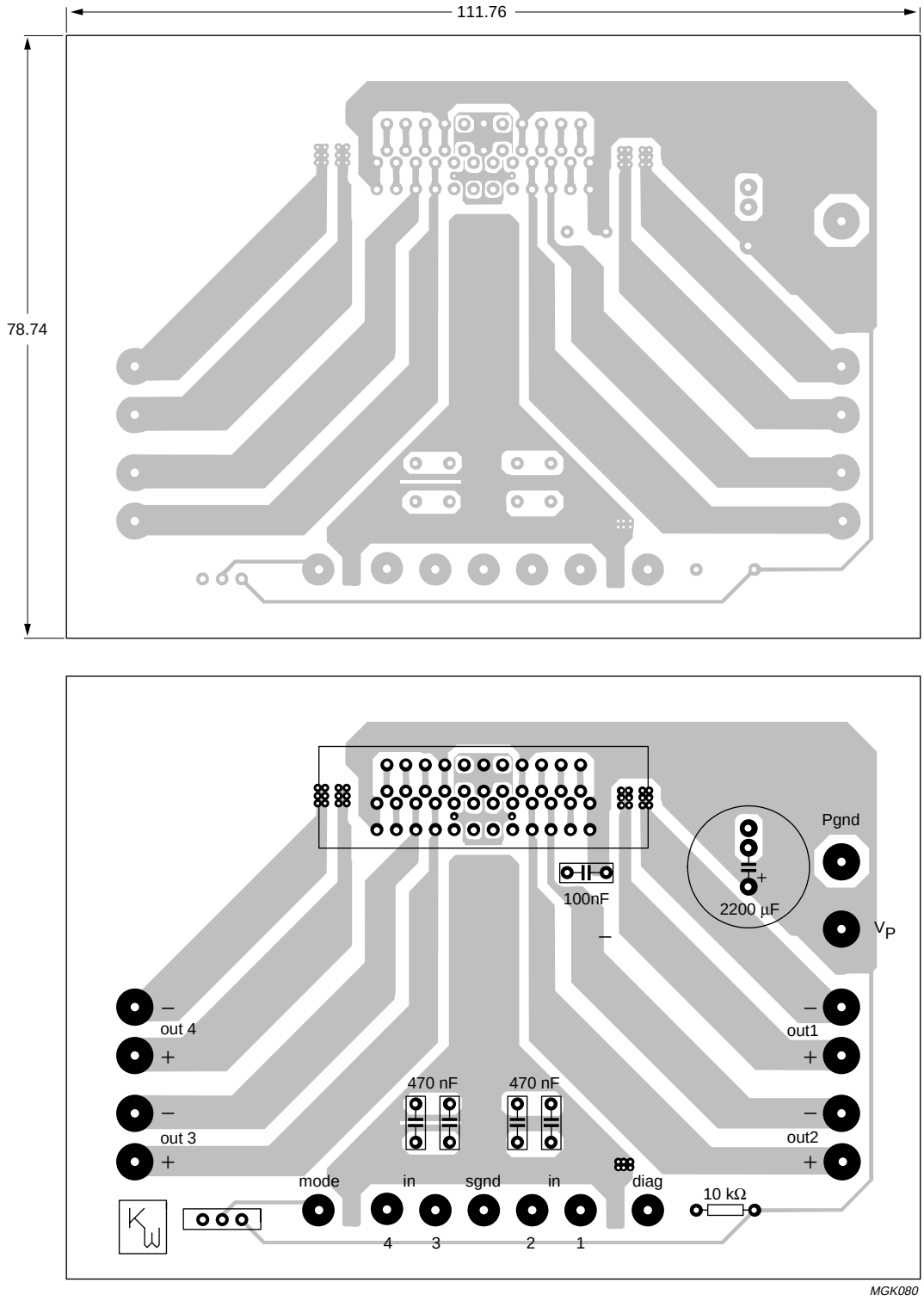
Fig.13 Channel separation as a function of frequency.

PCB layout



Dimensions in mm.

Fig.14 PCB layout (component side).

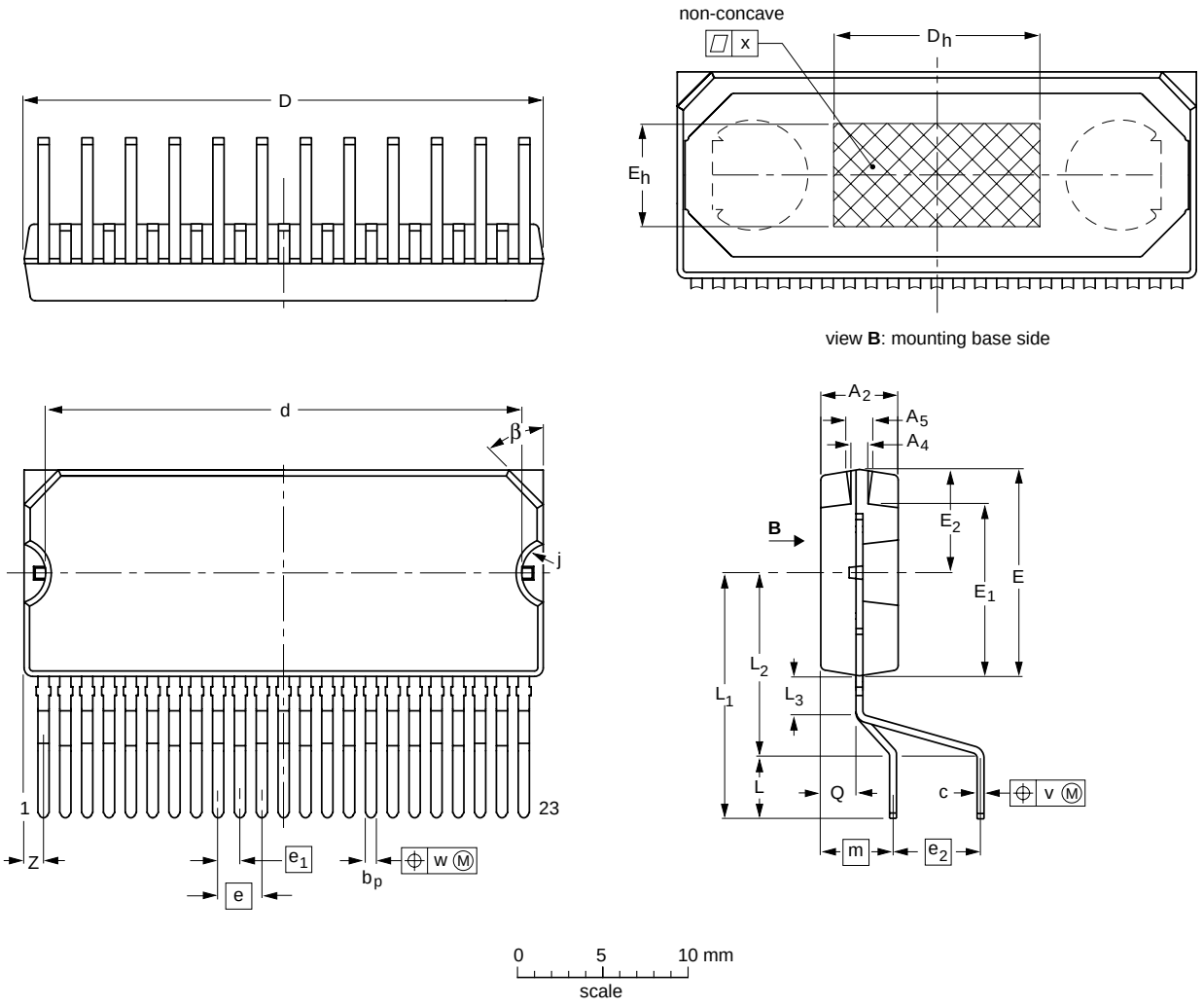


Dimensions in mm.

Fig.15 PCB layout (soldering side).

PACKAGE OUTLINE

DBS23P: plastic DIL-bent-SIL power package; 23 leads (straight lead length 3.2 mm) **SOT411-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A_2	A_4	A_5	b_p	c	$D^{(1)}$	d	D_h	$E^{(1)}$	e	e_1	e_2	E_h	E_1	E_2	j	L	L_1	L_2	L_3	m	Q	v	w	x	β	$Z^{(1)}$
mm	4.6 4.3	1.15 0.85	1.65 1.35	0.75 0.60	0.55 0.35	30.4 29.9	28.0 27.5	12	12.2 11.8	2.54	1.27	5.08	6	10.15 9.85	6.2 5.8	1.85 1.65	3.6 2.8	14.0 13.0	10.7 9.9	2.4 1.6	4.3	2.1 1.8	0.6	0.25	0.03	45°	1.43 0.78

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT411-1						~~96-10-11~~ 98-02-20

SOLDERING

Introduction to soldering through-hole mount packages

This text gives a brief insight to wave, dip and manual soldering. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

Wave soldering is the preferred method for mounting of through-hole mount IC packages on a printed-circuit board.

Soldering by dipping or by solder wave

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joints for more than 5 seconds.

The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ($T_{stg(max)}$). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

Manual soldering

Apply the soldering iron (24 V or less) to the lead(s) of the package, either below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

Suitability of through-hole mount IC packages for dipping and wave soldering methods

PACKAGE	SOLDERING METHOD	
	DIPPING	WAVE
DBS, DIP, HDIP, SDIP, SIL	suitable	suitable[1]

Note

1. For SDIP packages, the longitudinal axis must be parallel to the transport direction of the printed-circuit board.

DATA SHEET STATUS

DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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